

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:
a substrate;~~and~~
_____ ~~an electrode~~electrode, the electrode being formed on the substrate, substrate;
~~wherein a through-hole is being formed through the electrode and the substrate~~
in a stacking direction of the electrode and the ~~substrate, substrate;~~
_____ ~~a conductive member being inserted into the through-hole, through-hole;~~
~~wherein an insulating material is, being disposed between the electrode and the~~
conductive member, the insulating material including a wall portion located higher than at
least the ~~electrode, and electrode;~~ and
_____ ~~at least an interlayer dielectric being formed between the substrate and the~~
~~electrode, the through-hole being formed in the interlayer dielectric, and surfaces of the~~
~~interlayer dielectric and substrate in the through-hole being formed to have a level difference~~
~~in a boundary area between the substrate and the interlayer dielectric,~~
~~wherein the conductive member is being formed over the wall portion of the~~
insulating material from the through-hole and ~~is being~~ connected with the electrode.
2. (Original) The semiconductor device as defined in claim 1,
wherein the insulating material is formed to cover an upper surface of the
electrode and a surface in the through-hole, and includes a connection hole for connecting at
least the electrode with the conductive member at a position differing from the through-hole,
the wall portion being disposed between the connection hole and the through-hole.
- 3-4. (Canceled)
5. (Original) The semiconductor device as defined in claim 1,

wherein the conductive member functions as a connection terminal which secures electrical connection in an axial direction of the through-hole.

6. (Original) The semiconductor device as defined in claim 1, wherein a part of the conductive member projects outward from the through-hole on a side of the substrate opposite to a side on which the electrode is formed.

7. (Original) A semiconductor device comprising a plurality of the semiconductor devices as defined in claim 1 which are stacked, each of the semiconductor devices being electrically connected through the conductive members.

8. (Original) A circuit board comprising the semiconductor device as defined in claim 1.

9. (Original) An electronic instrument comprising the circuit board as defined in claim 8.

10-15. (Canceled)